



DESCRIPTION

The SS080N68MT uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

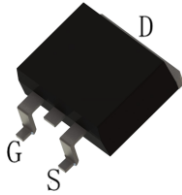
Application

- Power switching application
- Hard switched and High frequency ciutuits
- Uninterruptible power supply

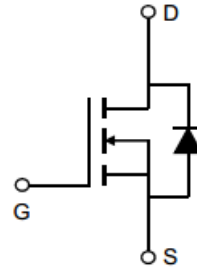
KEY CHARACTERISTICS

- $V_{DS} = 68V, I_D = 90A$
 $R_{DS(ON)} < 8m\Omega @ V_{GS}=10V$
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

100% UIS TESTED!
100% DVDS TESTED!



TO-263 Top View



Schematic diagram

Package Marking And Ordering Information

Device Marking	Ordering Codes	Package	Product Code	Packing
080N68MT	SS080N68MT	TO-263	SS080N68MT	REEL

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	68	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	90	A
Drain Current-Pulsed (Note 1)	I_{DM}	360	A
Maximum Power Dissipation($T_c=25^\circ C$)	P_D	125	W
Single pulse avalanche energy (Note 2)	E_{AS}	121	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.2	$^\circ C/W$
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